

深圳市晶泰源电子有限公司

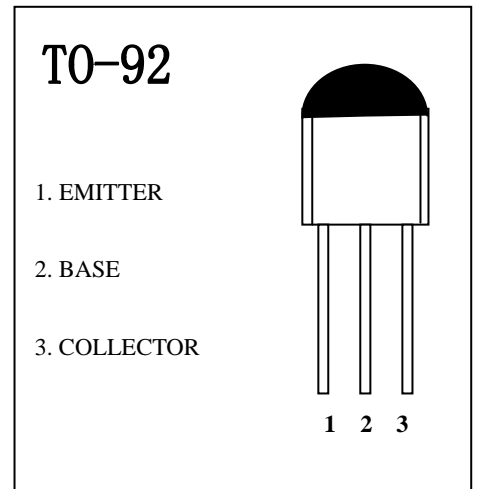
S9011 TRANSISTOR(NPN)

FEATURES

- Collector Current: $I_c=0.03A$

MAXIMUM RATINGS($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	50	V
VCEO	Collector-Emitter Voltage	30	V
VEBO	Emitter-Base Voltage	5	V
IC	Collector Current-Continuous	0.03	A
PC	Collector Power Dissipation	0.4	W
TJ	Junction Temperature	150	$^{\circ}C$
Tatg	Storage Temperature	-55-150	$^{\circ}C$



ELECTRICAL CHARACTERISTICS($T_{amb}=25^{\circ}C$ unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_c=1mA, I_E=0$	50			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_c=1mA, I_B=0$	30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_c=1mA, I_c=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=50V, I_E=0$			0.5	μA
Collector cut-off current	I_{CEO}	$V_{ce}=30V, I_B=0$			2.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_c=0$			0.1	μA
DC current gain	H_{FE}	$V_{ce}=5V, I_c=1mA$	28		198	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c=10mA, I_B=1mA$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c=10mA, I_B=1mA$			1.0	V
Gain Bandwidth Product	f_T	$V_{CE}=5V, I_c=1mA, f=30MHz$	150	370		MHz

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